Product Preview

Photodarlington Optocoupler with a Base-Emitter Resistor in a 4-Pin Full Pitch Mini-Flat Package

Description

The FODM352 consists of one gallium arsenide (GaAs) infrared light emitting diode, optically coupled to a photodarlington output with a base-emitter resistor, in a compact, mini-flat, 4-pin package. The input-output isolation voltage, V_{ISO}, is rated at 3,750 VAC_{RMS}.

- Current Transfer Ratio Min 1000% at I_F = 1 mA, $V_{CE} = 2 \text{ V}, T_{A} = 25^{\circ}\text{C}$
- Safety and Regulatory Approvals:
 - UL1577, 3750 VAC_{RMS} for 1 min
 - DIN EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage
- Applicable to Infrared Reflow, 260°C

Typical Applications

- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs
- Programmable Controllers

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.



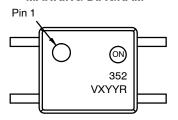
ON Semiconductor®

www.onsemi.com



MFP4 CASE 100AP

MARKING DIAGRAM



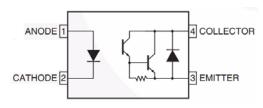
= Specific Device Code 352

= DIN EN/IEC60747-5-5 Option = One-Digit Year Code

ΥY = Work Week

R = Assembly Package Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

Table 1. SAFETY AND INSULATIONS RATING As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

| Parameter | Characteristics | |
|---|------------------------|-------|
| Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated | < 150 V _{RMS} | I–IV |
| Mains Voltage | < 300 V _{RMS} | I–III |
| Climatic Classification | 55/110/21 | |
| Pollution Degree (DIN VDE 0110/1.89) | 2 | |
| Comparative Tracking Index | 175 | |

| Symbol | Parameter | Value | Unit |
|-----------------------|--|-------------------|-------------------|
| V_{PR} | Input–to–Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC | 904 | V _{peak} |
| | Input–to–Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with t_m = 1 s, Partial Discharge < 5 pC | 1060 | V _{peak} |
| V _{IORM} | Maximum Working Insulation Voltage | 565 | V _{peak} |
| V_{IOTM} | Highest Allowable Over-Voltage | 6,000 | V _{peak} |
| | External Creepage | ≥ 5 | mm |
| | External Clearance | ≥ 5 | mm |
| DTI | Distance Through Insulation (Insulation Thickness) | ≥ 0.4 | mm |
| T _S | Case Temperature (Note 1) | 150 | °C |
| I _{S,INPUT} | Input Current (Note 1) | 200 | mA |
| P _{S,OUTPUT} | Output Power (Note 1) | 300 | mW |
| R _{IO} | Insulation Resistance at T _S , V _{IO} = 500 V (Note 1) | > 10 ⁹ | Ω |

^{1.} Safety limit values - maximum values allowed in the event of a failure.

Table 2. ABSOLUTE MAXIMUM RATINGS (Note 2) $T_A = 25$ °C unless otherwise specified.

| Symbol | Parameter | Value | Units |
|-------------------------|---|----------------|-------|
| T _{STG} | Storage Temperature | -55 to +150 | °C |
| T _{OPR} | Operating Temperature | -55 to +110 | °C |
| TJ | Junction Temperature | -55 to +125 | °C |
| T _{SOL} | Lead Solder Temperature (Refer to Reflow Temperature Profile) | 260 for 10 sec | °C |
| MITTER | | | |
| I _{F(average)} | Continuous Forward Current | 50 | mA |
| V_{R} | Reverse Input Voltage | 6 | V |
| PD_{LED} | Power Dissipation (Note 3) | 70 | mW |
| TECTOR | | | |
| I _{C(average)} | Continuous Collector Current | 150 | mA |
| V_{CEO} | Collector-Emitter Voltage | 300 | V |
| V _{ECO} | Emitter-Collector Voltage | 0.1 | V |
| PD_C | Collector Power Dissipation (Note 3) | 150 | mW |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

^{2.} Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.

Table 3. ELECTRICAL CHARACTERISTICS T_A = 25°C unless otherwise specified

| Symbol | Parameter | Conditions | Min | Тур | Max | Units |
|-------------------|-------------------------------------|--|-----|-----|-----|-------|
| EMITTER | | | | | | |
| V_{F} | Forward Voltage | ^I F = 10 mA | | 1.2 | 1.4 | V |
| I _R | Reverse Current | V _R = 4 V | | | 10 | μΑ |
| C _T | Terminal Capacitance | V = 0 V, f = 1 kHz | | 30 | 250 | pF |
| DETECTOR | | | | | | |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | I _C = 0.1 mA, I _F = 0 mA | 300 | | | V |
| BV _{ECO} | Emitter-Collector Breakdown Voltage | $I_E = 10 \mu A, I_F = 0 \text{ mA}$ | 0.1 | | | V |
| I _{CEO} | Collector Dark Current | V _{CE} = 200 V, I _F = 0 mA | | | 200 | nA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Table 4. TRANSFER CHARACTERISTICS $T_A = 25^{\circ}C$ unless otherwise specified

| Symbol | Parameter | Conditions | Min | Тур | Max | Units |
|----------------------|--------------------------------------|--|------|------|-----|-------|
| I _C | Collector Current | I _F = 1 mA, V _{CE} = 2 V | 10 | | | mA |
| CTR | Current Transfer Ratio | $I_F = 1 \text{ mA}, V_{CE} = 2 \text{ V}$ | 1000 | 5000 | | % |
| V _{CE(SAT)} | Collector-Emitter Saturation Voltage | $I_F = 20 \text{ mA}, I_C = 100 \text{ mA}$ | | | 1.2 | V |

Table 5. SWITCHING CHARACTERISTICS $T_A = 25^{\circ}C$ unless otherwise specified

| Symbol | Parameter | Conditions | Min | Тур | Max | Units |
|----------------|-----------------------------|--|-----|-----|-----|-------|
| t _R | Output Rise Time (10% –90%) | $I_F = 20 \text{ mA}, V_{CC} = 2 \text{ V},$ $R_L = 100 \ \Omega$ | | 20 | 100 | μs |
| t _F | Output Fall Time (90% –10%) | $I_F = 20 \text{ mA}, \ V_{CC} = 2 \text{ V}, \\ R_L = 100 \ \Omega$ | | 100 | 300 | μs |

Table 6. ISOLATION CHARACTERISTICS

| Symbol | Parameter | Conditions | Min | Тур | Max | Units |
|------------------|--------------------------------|--|----------------------|-----|-----|--------------------|
| V _{ISO} | Input-Output Isolation Voltage | Freq = 60 Hz, t = 1.0 min, $I_{I-O} \le 10 \mu A$ (Notes 4, 5) | 3,750 | | | VAC _{RMS} |
| R _{ISO} | Isolation Resistance | V _{I-O} = 500 V (Note 4) | 5 x 10 ¹⁰ | | | Ω |
| C _{ISO} | Isolation Capacitance | Frequency = 1 MHz | | 0.6 | 1.0 | pF |

^{4.} Device is considered a two terminal device: Pin 1 and 2 are shorted together and Pins 3 and 4 are shorted together.

ORDERING INFORMATION

| Part Number | Package | Packing Method |
|-------------|--|----------------------------|
| FODM352 | SOP 4-Pin | Tube (100 units) |
| FODM352R2 | SOP 4-Pin | Tape and Reel (2500 units) |
| FODM352V | SOP 4-Pin, DIN EN/IEC60747-5-5 Option (pending approval) | Tube (100 units) |
| FODM352R2V | SOP 4-Pin, DIN EN/IEC60747-5-5 Option (pending approval) | Tape and Reel (2500 units) |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{5.} $3,750 \text{ VAC}_{RMS}$ for 1 minute duration is equivalent to $4,500 \text{ VAC}_{RMS}$ for 1 second duration.

TYPICAL CHARACTERISTICS

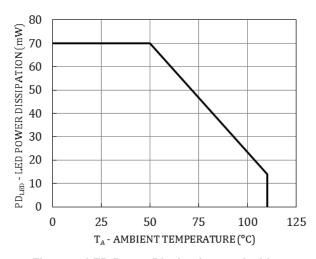


Figure 1. LED Power Dissipation vs. Ambient Temperature

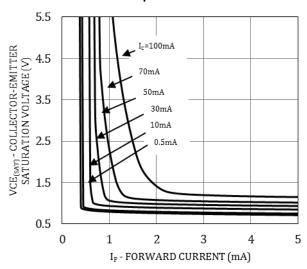


Figure 3. Collector Emitter Saturation Voltage vs. Forward Current

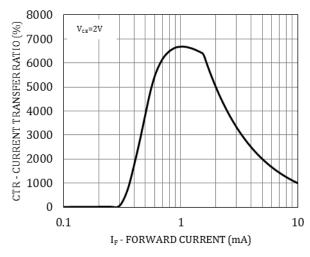


Figure 5. Current Transfer Ratio vs. Forward Current

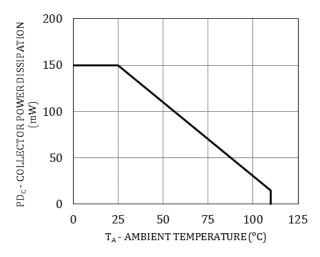


Figure 2. Collector Power Dissipation vs.
Ambient Temperature

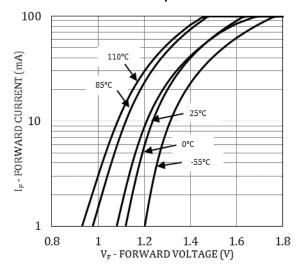


Figure 4. Forward Current vs. Forward Voltage

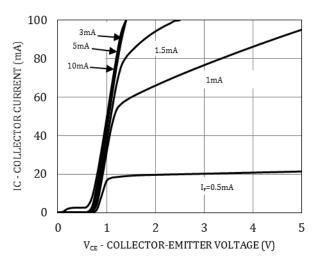


Figure 6. Collector Current vs. Collector Emitter Voltage

TYPICAL CHARACTERISTICS

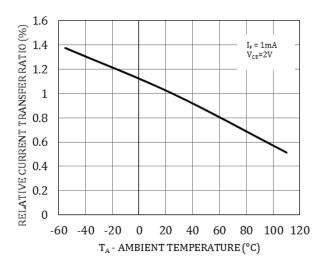


Figure 7. Relative Current Transfer Ratio vs.

Ambient Temperature

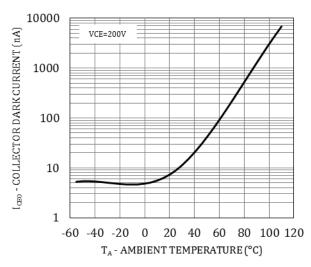


Figure 9. Collector Dark Current vs. Ambient
Temperature

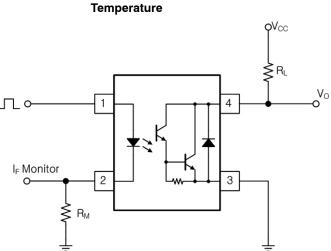


Figure 11. Test Circuit for Switching Time

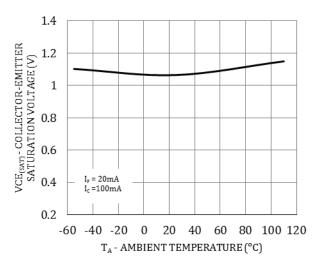


Figure 8. Collector Emitter Saturation Voltage vs. Ambient Temperature

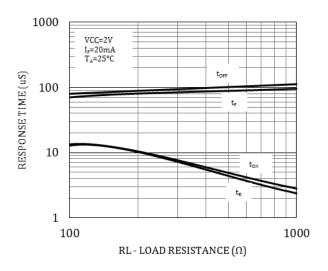
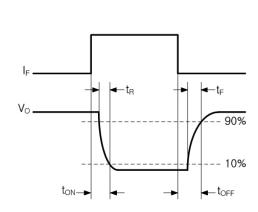


Figure 10. Response Time vs. Load Resistance



REFLOW PROFILE

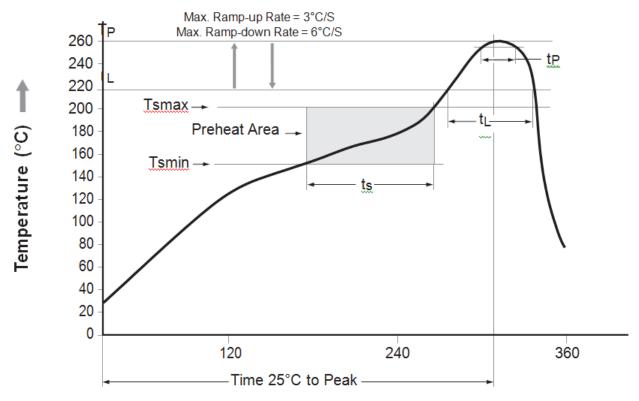
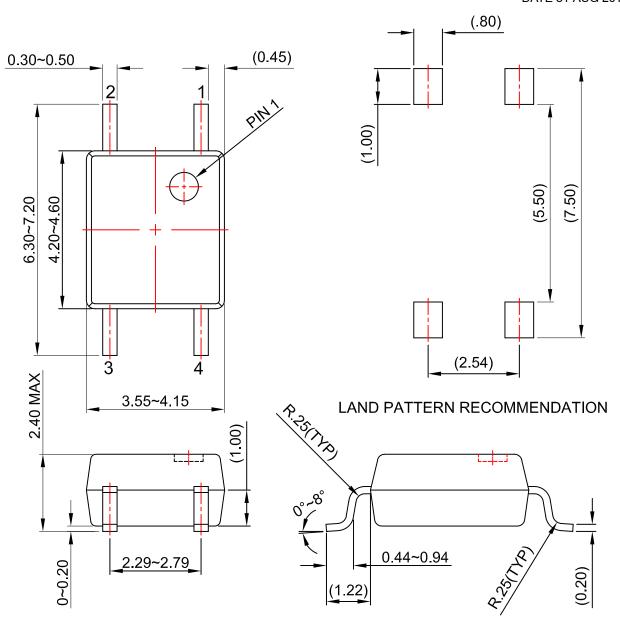


Figure 12. Reflow Profile

| Profile Feature | Pb-Free Assembly Profile |
|---|--------------------------|
| Temperature Min. (Tsmin) | 150°C |
| Temperature Max. (Tsmax) | 200°C |
| Time (t _S) from (Tsmin to Tsmax) | 60-120 seconds |
| Ramp-up Rate (t _L to t _P) | 3°C/second max. |
| Liquidous Temperature (T _L) | 217°C |
| Time (t _L) Maintained Above (T _L) | 60-150 seconds |
| Peak Body Package Temperature | 260°C +0°C / -5°C |
| Time (t _P) within 5°C of 260°C | 30 seconds |
| Ramp-down Rate (T _P to T _L) | 6°C/second max. |
| Time 25°C to Peak Temperature | 8 minutes max. |

MFP4 3.85X4.4, 2.54P CASE 100AP ISSUE O

DATE 31 AUG 2016



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION

| DOCUMENT NUMBER: | 98AON13488G | Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | | | |
|------------------|----------------------|---|-------------|--|--|
| DESCRIPTION: | MFP4 3.85X4.4, 2.54P | | PAGE 1 OF 1 | | |

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative